

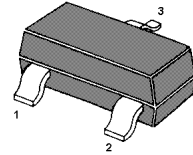
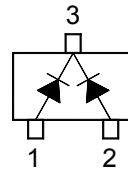
BAV70 Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching application


 Marking Code: **A4**
SOT-23 Plastic Package

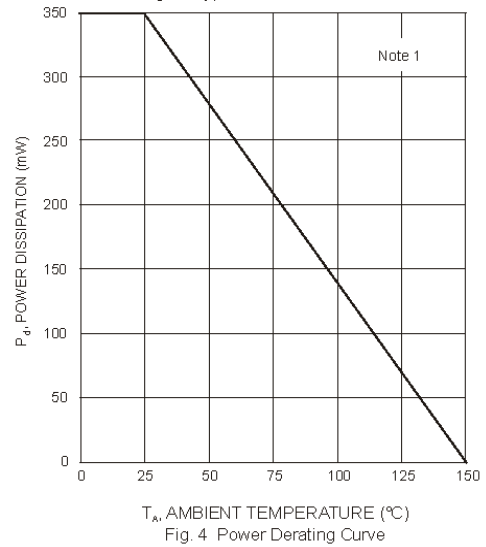
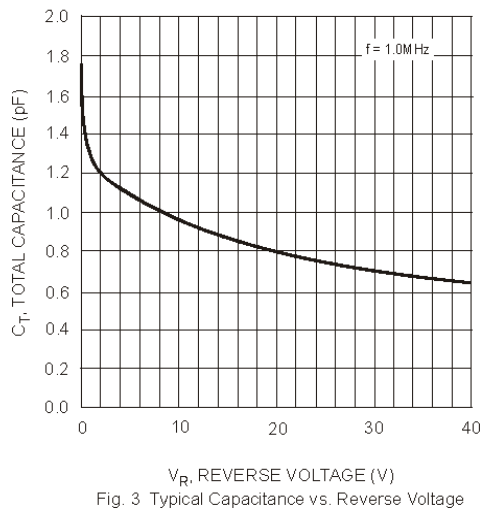
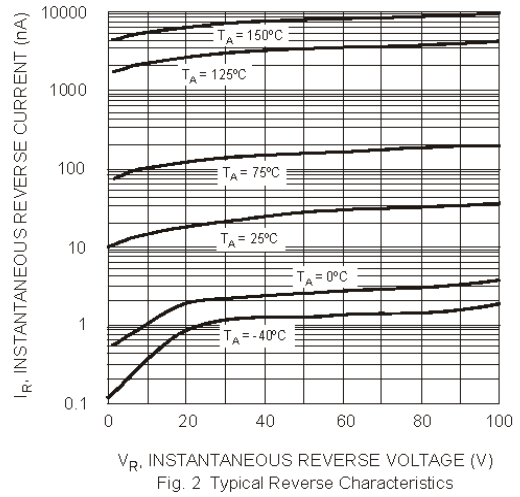
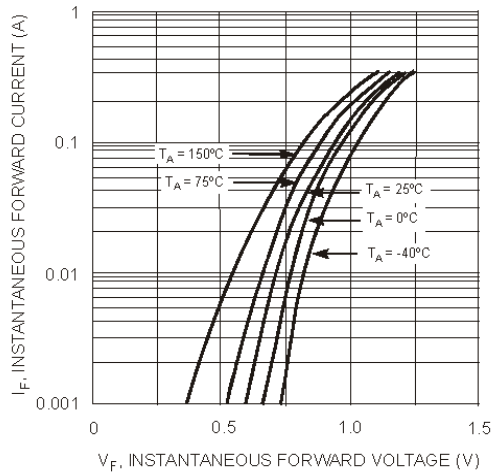
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Maximum Peak Reverse Voltage	V_{RM}	100	V	
Reverse Voltage	V_R	75	V	
Average Forward Current	I_O	200	mA	
Maximum Peak Forward Current	I_{FM}	300	mA	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$	1	A
		at $t = 1\text{ }\mu\text{s}$	2	
Power Dissipation	P_d	350	mW	
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$	

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
Forward Voltage	V_F	at $I_F = 1\text{ mA}$	-	715	mV
		at $I_F = 10\text{ mA}$	-	855	mV
		at $I_F = 50\text{ mA}$	-	1	V
		at $I_F = 150\text{ mA}$	-	1.25	V
Reverse Current	I_R	at $V_R = 20\text{ V}$	-	25	nA
		at $V_R = 75\text{ V}$	-	2.5	μA
		at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	30	μA
		at $V_R = 75\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	50	μA
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V	
Total Capacitance	C_T	-	2	pF	
Reverse Recovery Time	t_{rr}	-	4	ns	
at $I_F = I_R = 10\text{ mA}$ to $I_{rr} = 1\text{ mA}$, $R_L = 50\text{ }\Omega$					

BAV70



Note: Specification is subject to change without further notice. For more details and updates, please visit our website.